**Product data sheet** 

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Very low threshold voltage
- Very fast switching
- · Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection typically > 2 kV
- Ultra thin package profile of 0.37 mm

## 3. Applications

- Relay driver
- · High-speed line driver
- · High-side load switch
- · Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-12	V
$V_{GS}$	gate-source voltage			-6	-	6	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	-1.2	Α
Static chara	acteristics						
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -1.2 \text{ A}; T_j = 25 \text{ °C}$		-	300	355	mΩ
	resistance	$V_{GS}$ = -1.8 V; $I_D$ = -0.1 A; $T_j$ = 25 °C		-	540	820	mΩ

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.



12 V, P-channel Trench MOSFET

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D
2	S	source		
3	D	drain		G L
			1 2	
			Transparent top view	s
			DFN1006B-3 (SOT883B)	017aaa259

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package							
	Name	Description	Version					
PMZB220VPE		plastic, leadless ultra small plastic package; 3 solder lands; 0.35 mm pitch; 1.0 mm x 0.6 mm x 0.37 mm body	SOT883B					

## 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PMZB220VPE	1001
	1101

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# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-12	V
$V_{GS}$	gate-source voltage			-6	6	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-1.2	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-10.4	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	340	mW
			[1]	-	690	mW
		T <sub>sp</sub> = 25 °C		-	3.5	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain	diode				·	
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	-0.63	А

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

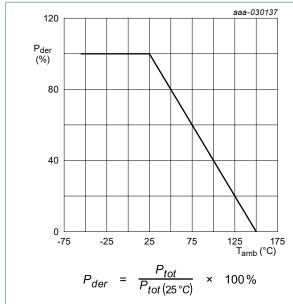


Fig. 1. Normalized total power dissipation as a function of ambient temperature

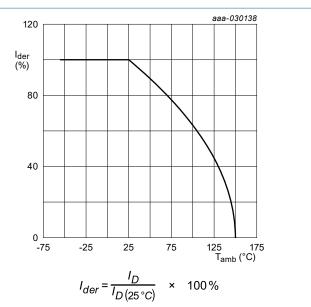


Fig. 2. Normalized continuous drain current as a function of ambient temperature

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### 12 V, P-channel Trench MOSFET

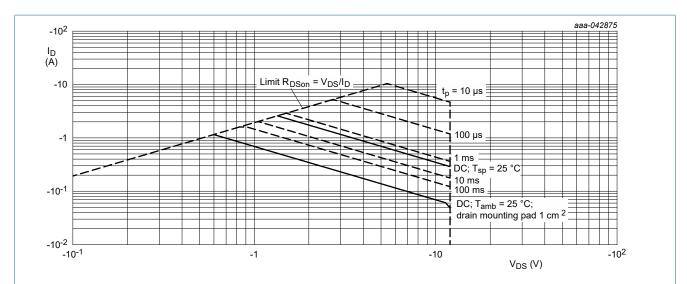


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

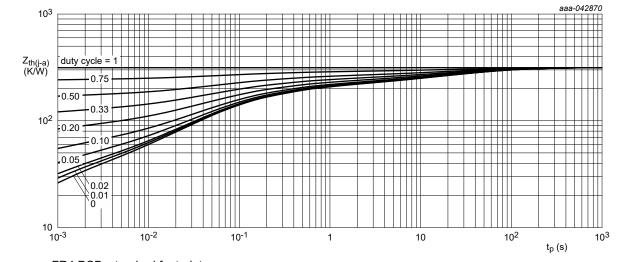
12 V, P-channel Trench MOSFET

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

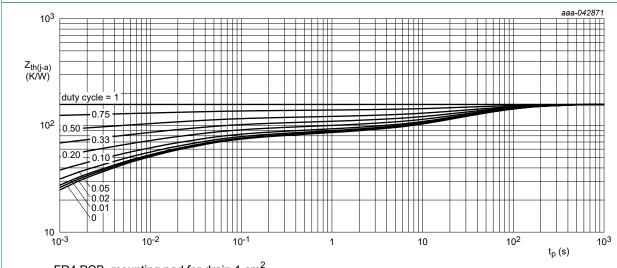
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	315	363	K/W
	junction to ambient		[2]	-	157	181	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	29	36	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm<sup>2</sup>

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-12	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-0.35	-0.57	-0.83	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = -10 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -6 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		V <sub>GS</sub> = 6 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		$V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-1.5	μΑ
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1.5	μA
		$V_{GS} = -2.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-500	nA
		V <sub>GS</sub> = 2.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	500	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -1.2 \text{ A}; T_j = 25 \text{ °C}$	-	300	355	mΩ
		V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -1.2 A; T <sub>j</sub> = 150 °C	-	440	520	mΩ
		$V_{GS} = -2.5 \text{ V}; I_D = -1 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	430	600	mΩ
		V <sub>GS</sub> = -1.8 V; I <sub>D</sub> = -0.1 A; T <sub>j</sub> = 25 °C	-	540	820	mΩ
		$V_{GS} = -1.5 \text{ V}; I_D = -0.01 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	630	1400	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS} = -5 \text{ V}; I_D = -1.2 \text{ A}; T_j = 25 \text{ °C}$	-	1.9	-	S
Dynamic ch	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -6 V; $I_{D}$ = -1.2 A; $V_{GS}$ = -4.5 V;	-	0.9	1.4	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.1	-	nC
Q <sub>GD</sub>	gate-drain charge		-	0.3	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -6 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	67.8	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	20.1	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	17.7	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = -6 \text{ V}; I_D = -1.2 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	1	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	8	-	ns
t <sub>f</sub>	fall time	1	-	6	-	ns
Source-dra	in diode		1			
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -0.52 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	-0.7	-1.2	V

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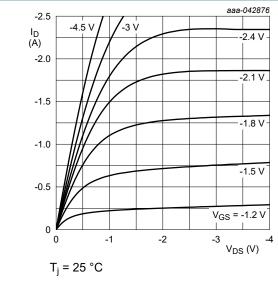


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

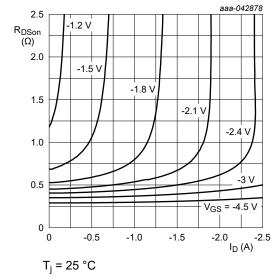


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

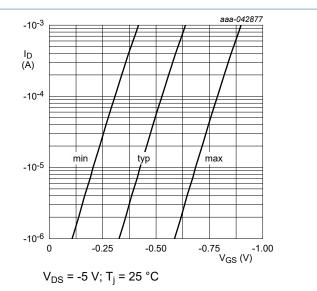


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

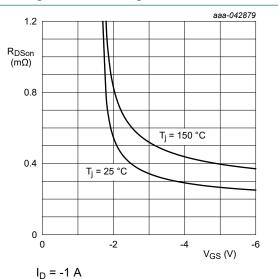


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

### 12 V, P-channel Trench MOSFET

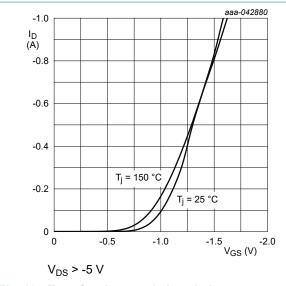


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

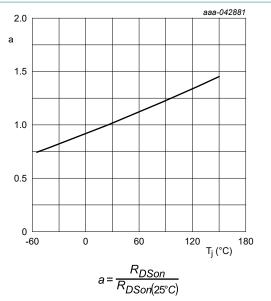


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

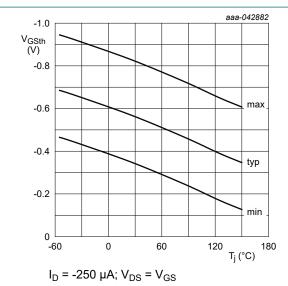
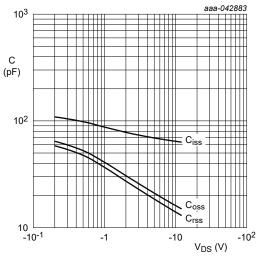


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

### 12 V, P-channel Trench MOSFET

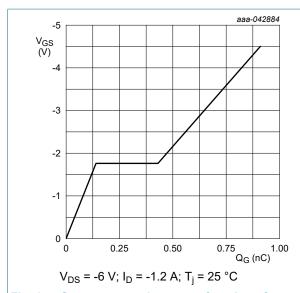


Fig. 14. Gate-source voltage as a function of gate charge; typical values

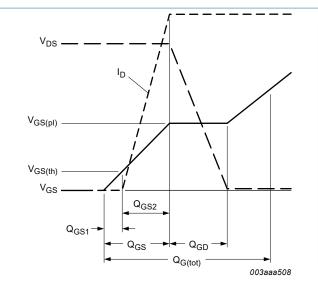


Fig. 15. Gate charge waveform definitions

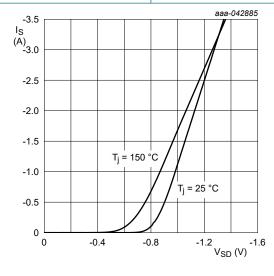
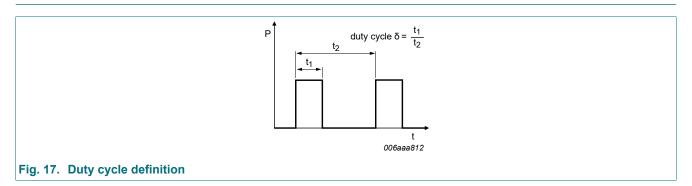


Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

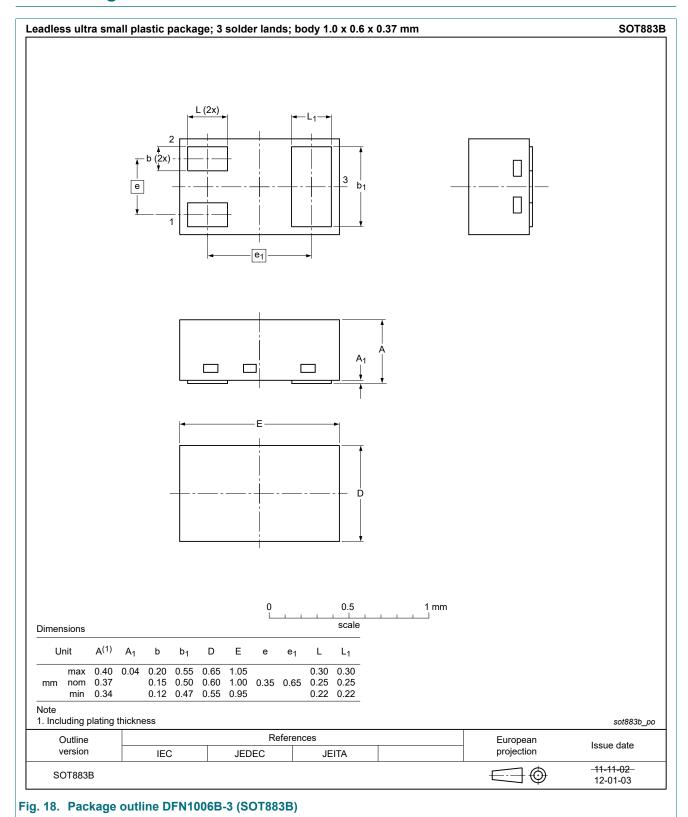
 $V_{GS} = 0 V$ 



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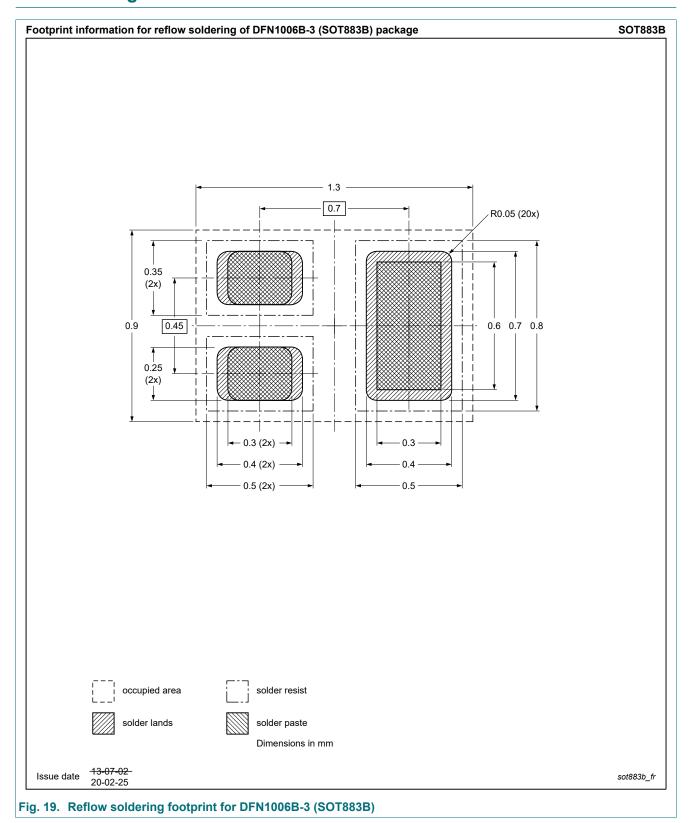
12 V, P-channel Trench MOSFET

# 12. Package outline



12 V, P-channel Trench MOSFET

# 13. Soldering



12 V, P-channel Trench MOSFET

# 14. Revision history

### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMZB220VPE v.1	20250616	Product data sheet	-	-

### 12 V, P-channel Trench MOSFET

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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	Features and benefits

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